



SPICE Device Model SUD15N15-95

Vishay Siliconix

N-Channel 150-V (D-S) 175° MOSFET

CHARACTERISTICS

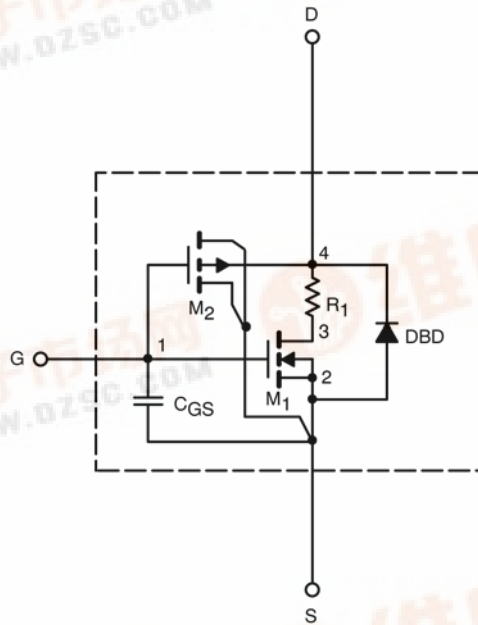
- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to 125°C temperature ranges under the pulsed 0 to 10V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

SUBCIRCUIT MODEL SCHEMATIC



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| SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED) | | | | | |
|---|---------------------|--|----------------|---------------|------|
| Parameter | Symbol | Test Conditions | Simulated Data | Measured Data | Unit |
| Static | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 2.6 | | V |
| On-State Drain Current ^b | I _{D(on)} | V _{DS} = 5 V, V _{GS} = 10 V | 71 | | A |
| Drain-Source On-State Resistance ^b | r _{DS(on)} | V _{GS} = 10 V, I _D = 15 A | 0.069 | 0.077 | Ω |
| | | V _{GS} = 10 V, I _D = 15 A, T _J = 125°C | 0.115 | | |
| | | V _{GS} = 10 V, I _D = 15 A, T _J = 175°C | 0.139 | | |
| | | V _{GS} = 6 V, I _D = 10 A | 0.080 | 0.081 | |
| Forward Voltage ^b | V _{SD} | I _S = 15 A, V _{GS} = 0 V | 0.89 | 0.90 | V |
| Dynamic^a | | | | | |
| Input Capacitance | C _{iss} | V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz | 897 | 900 | pF |
| Output Capacitance | C _{oss} | | 126 | 115 | |
| Reverse Transfer Capacitance | C _{rss} | | 73 | 70 | |
| Total Gate Charge ^c | Q _g | V _{DS} = 75 V, V _{GS} = 10 V, I _D = 15 A | 21 | 20 | nC |
| Gate-Source Charge ^c | Q _{gs} | | 5.5 | 5.5 | |
| Gate-Drain Charge ^c | Q _{gd} | | 7 | 7 | |
| Turn-On Delay Time ^c | t _{d(on)} | V _{DD} = 75 V, R _L = 5 Ω I _D ≅ 15 A, V _{GEN} = 10 V, R _G = 2.5 Ω | 12 | 8 | ns |
| Rise Time ^c | t _r | | 19 | 35 | |
| Turn-Off Delay Time ^c | t _{d(off)} | | 36 | 17 | |
| Fall Time ^c | t _f | | 41 | 30 | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 15 A, di/dt = 100 A/μs | 48 | 55 | |

Notes

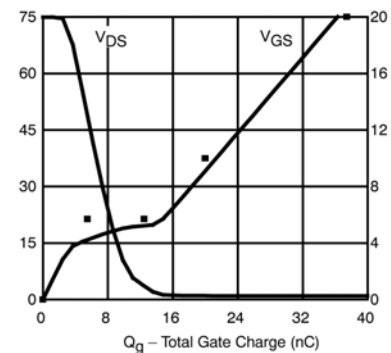
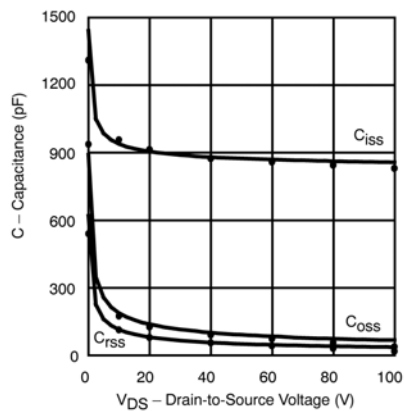
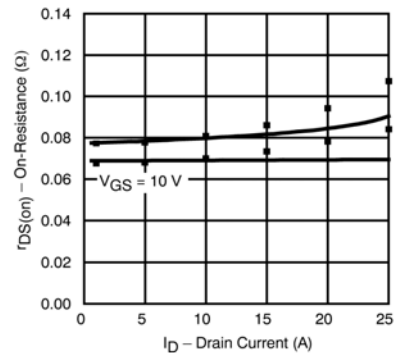
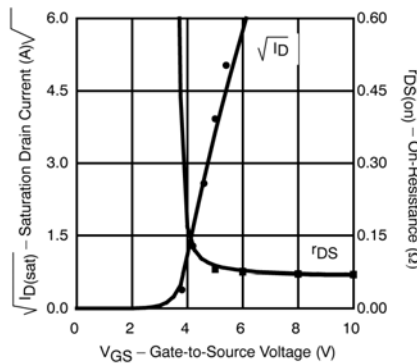
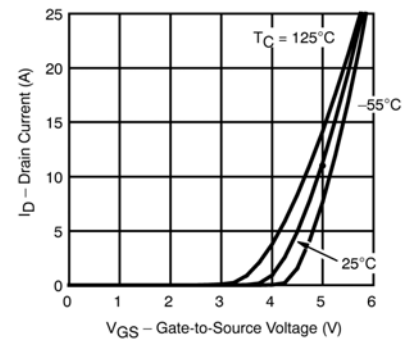
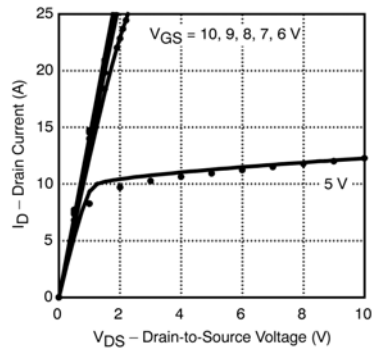
- Guaranteed by design, not subject to production testing.
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Independent of operating temperature.



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COMPARISON OF MODEL WITH MEASURED DATA ($T_J=25^\circ\text{C}$ UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.